

DATA SHEET

BLW898 UHF linear power transistor

Product specification
Supersedes data of 1995 Oct 04

1996 Jul 16

UHF linear power transistor

BLW898

FEATURES

- Internal input matching for wideband operation and high power gain
- Polysilicon emitter ballasting resistors for an optimum temperature profile
- Gold metallization ensures excellent reliability.

APPLICATION

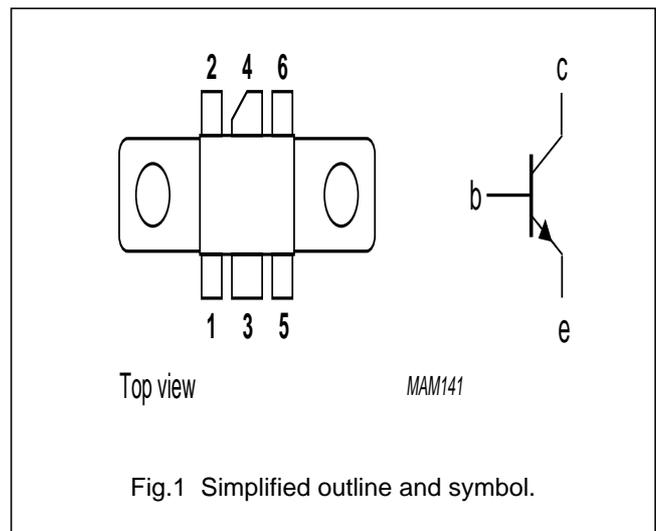
- Common emitter class-A operation in linear transposers/transmitters (television) in the 470 to 860 MHz frequency band.

DESCRIPTION

NPN silicon planar transistor in a SOT171A 6-lead rectangular flange package, with a ceramic cap. The transistor delivers a $P_{o\ sync} = 3\text{ W}$ in class-A operation at 860 MHz and a supply voltage of 25 V.

PINNING SOT171A

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | emitter |
| 2 | emitter |
| 3 | base |
| 4 | collector |
| 5 | emitter |
| 6 | emitter |



QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ °C}$ in a common emitter test circuit.

| MODE OF OPERATION | f (MHz) | V_{CE} (V) | I_{CQ} (A) | $P_{o\ sync}$ (W) | G_p (dB) |
|-------------------|---------|--------------|--------------|-------------------|----------------|
| CW class-A | 860 | 25 | 1.1 | $\geq 3^{(1)}$ | $\geq 9^{(1)}$ |

Note

1. Three-tone test signal (-8, -16, and -10 dB); $d_{im} = -63\text{ dB}$.

| WARNING |
|--|
| Product and environmental safety - toxic materials |
| This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste. |

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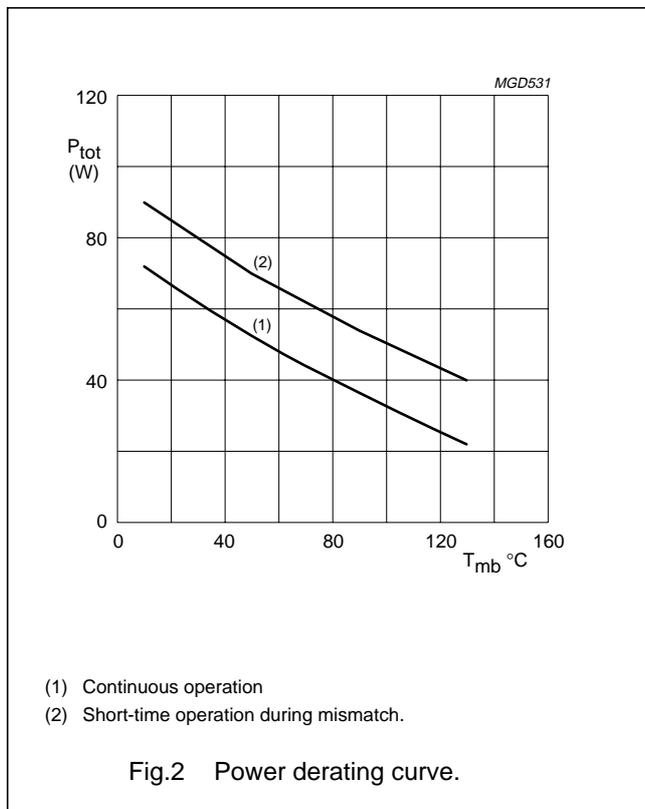
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------------|--------------------------------|-------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | – | 60 | V |
| V _{CEO} | collector-emitter voltage | open base | – | 28 | V |
| V _{EBO} | emitter-base voltage | open collector | – | 2.5 | V |
| I _C | collector current (DC) | | – | 3.7 | A |
| I _{C(AV)} | average collector current | | – | 3.7 | A |
| P _{tot} | total power dissipation | up to T _{mb} = 70 °C | – | 44 | W |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | operating junction temperature | | – | 200 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|--|-------|------|
| R _{th j-mb} | thermal resistance from junction to mounting-base | P _{tot} = 44 W; T _{mb} = 70 °C | 3 | K/W |
| R _{th mb-h} | thermal resistance from mounting-base to heatsink | | 0.3 | K/W |



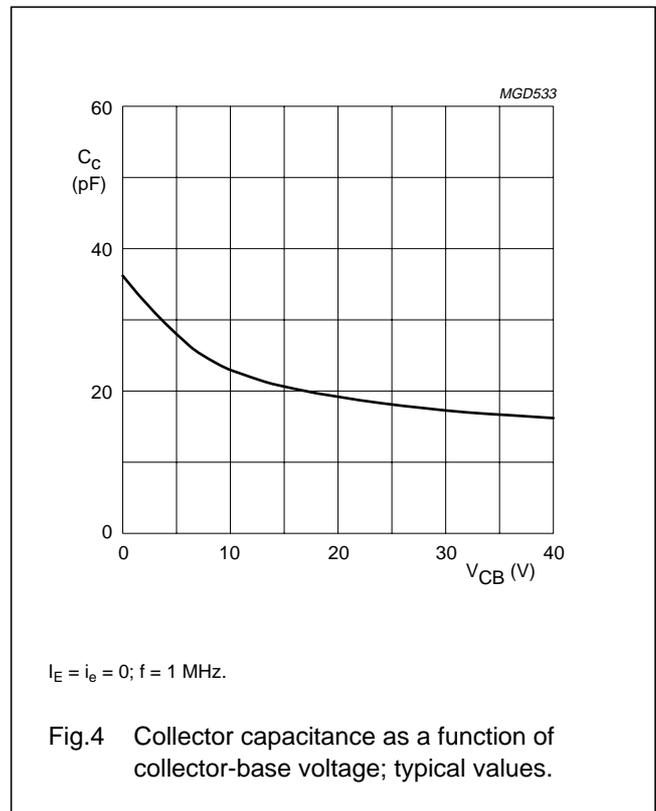
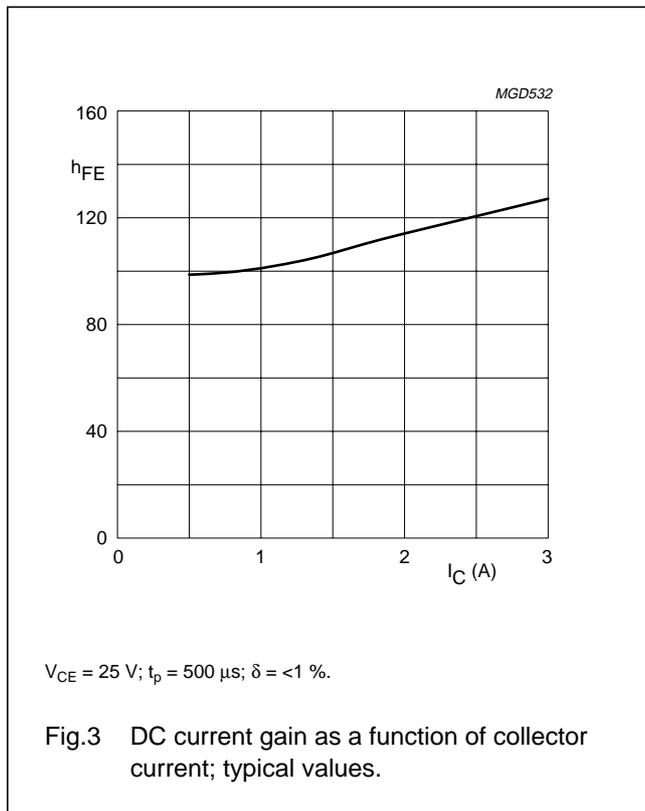
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CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------|-------------------------------------|--|------|------|------|------|
| $V_{(BR)CBO}$ | collector-base breakdown voltage | $I_C = 15\text{ mA}; I_E = 0$ | 60 | – | – | V |
| $V_{(BR)CEO}$ | collector-emitter breakdown voltage | $I_C = 30\text{ mA}; I_B = 0$ | 28 | – | – | V |
| $V_{(BR)EBO}$ | emitter-base breakdown voltage | $I_E = 0.6\text{ mA}; I_C = 0$ | 2.5 | – | – | V |
| I_{CBO} | collector-base leakage current | $V_{BE} = 0; V_{CB} = 28\text{ V}$ | – | – | 1.5 | mA |
| I_{CEO} | collector-emitter leakage current | $V_{CE} = 20\text{ V}$ | – | – | 3 | mA |
| h_{FE} | DC current gain | $V_{CE} = 25\text{ V}; I_C = 1.1\text{ A}$ | 30 | – | 140 | |
| C_c | collector capacitance | $V_{CB} = 25\text{ V}; I_E = i_e = 0;$ $f = 1\text{ MHz}$ | – | 18 | – | pF |
| C_{re} | feedback capacitance | $V_{CB} = 25\text{ V}; I_C = 0; f = 1\text{ MHz}$ | – | 11 | – | pF |



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APPLICATION INFORMATION

RF performance at $T_h = 25\text{ }^\circ\text{C}$ in a common emitter class-A test circuit.

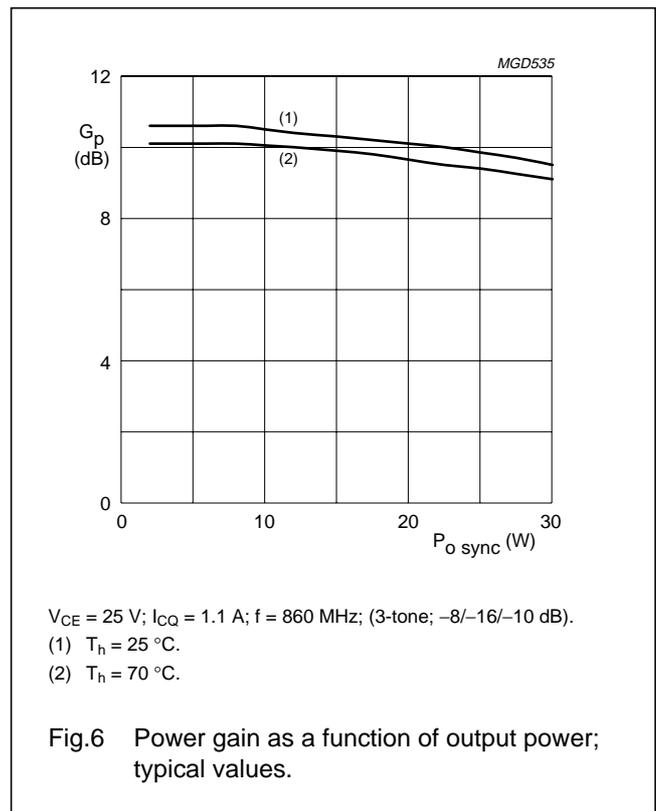
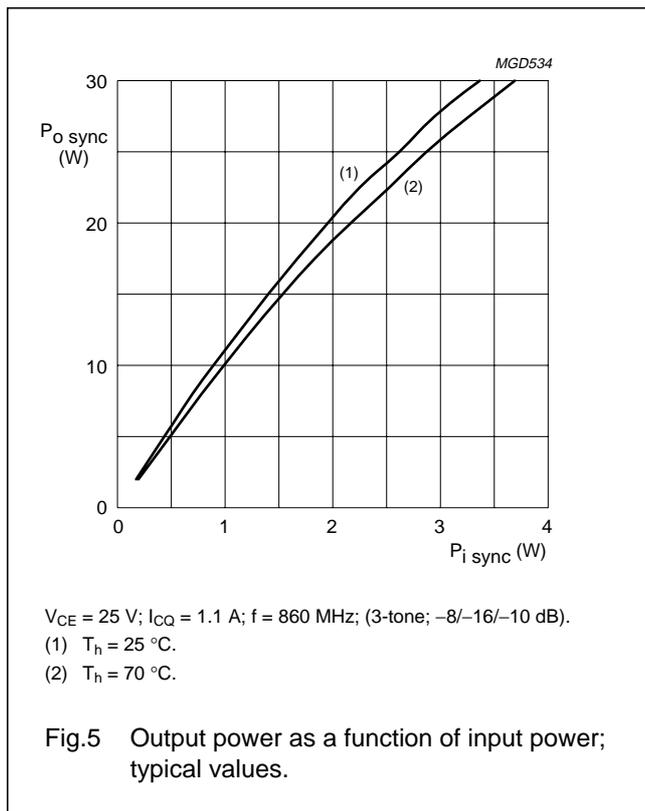
| MODE OF OPERATION | f (MHz) | V_{CE} (V) | I_{CQ} (A) | $P_{O\text{ sync}}$ (W) | G_p (dB) | d_{im} (dB) |
|-------------------|---------|--------------|--------------|-------------------------|----------------|---------------|
| CW class-A | 860 | 25 | 1.1 | $\geq 3^{(1)}$ | $\geq 9^{(1)}$ | $< -63^{(1)}$ |
| CW class-A | 860 | 25 | 1.1 | $\geq 3^{(2)}$ | $\geq 9^{(2)}$ | $< -60^{(2)}$ |

Notes

- Three-tone test method (vision carrier -8 dB , sound carrier -10 dB , sideband signal -16 dB), 0 dB corresponds to peak sync level.
- Three-tone test method (vision carrier -8 dB , sound carrier -7 dB , sideband signal -16 dB), 0 dB corresponds to peak sync level.

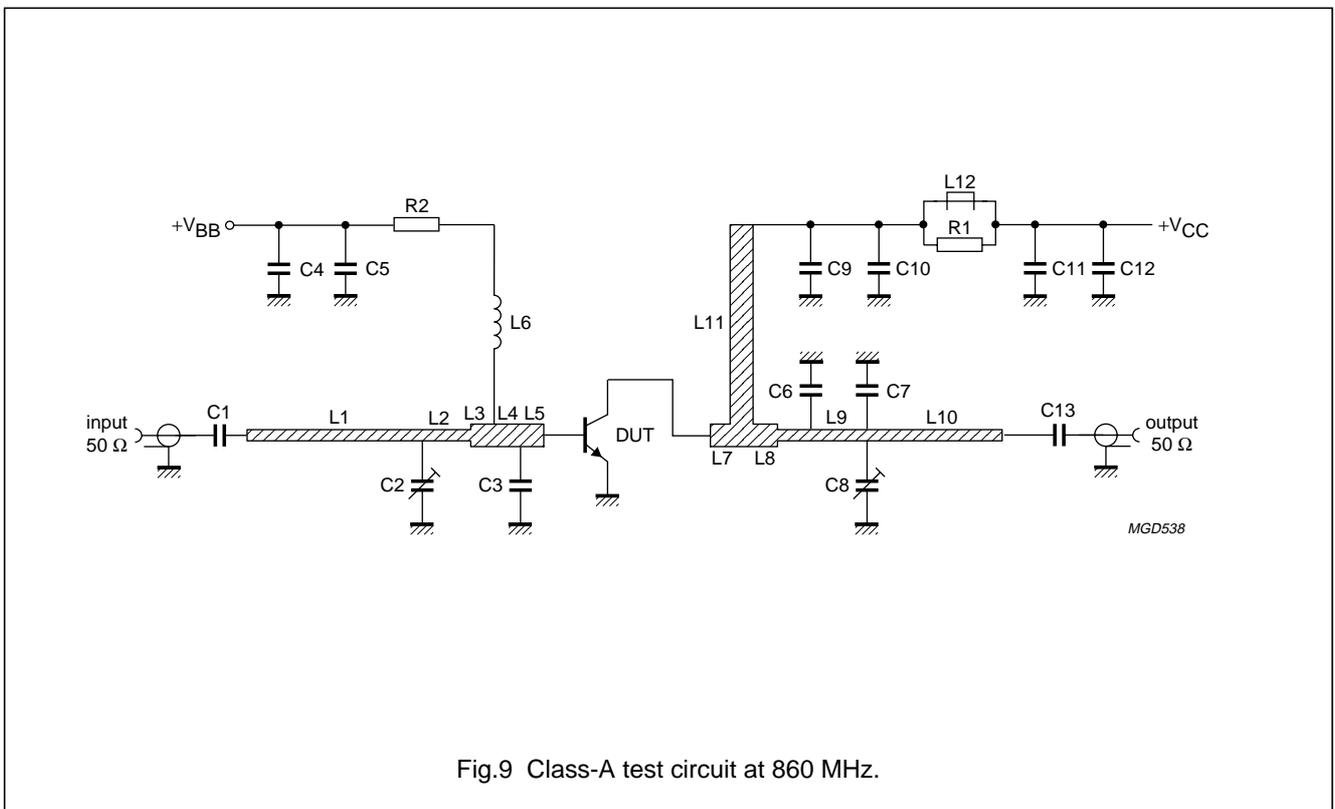
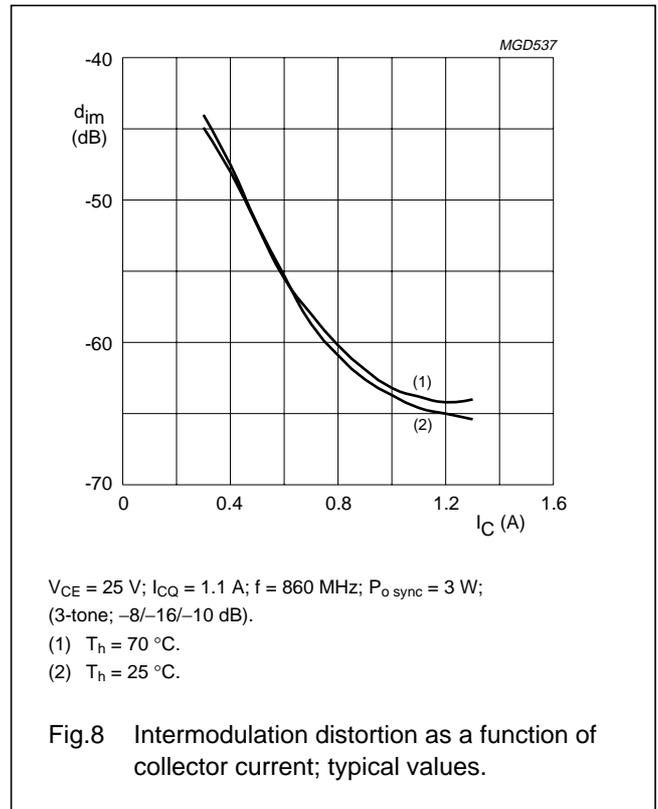
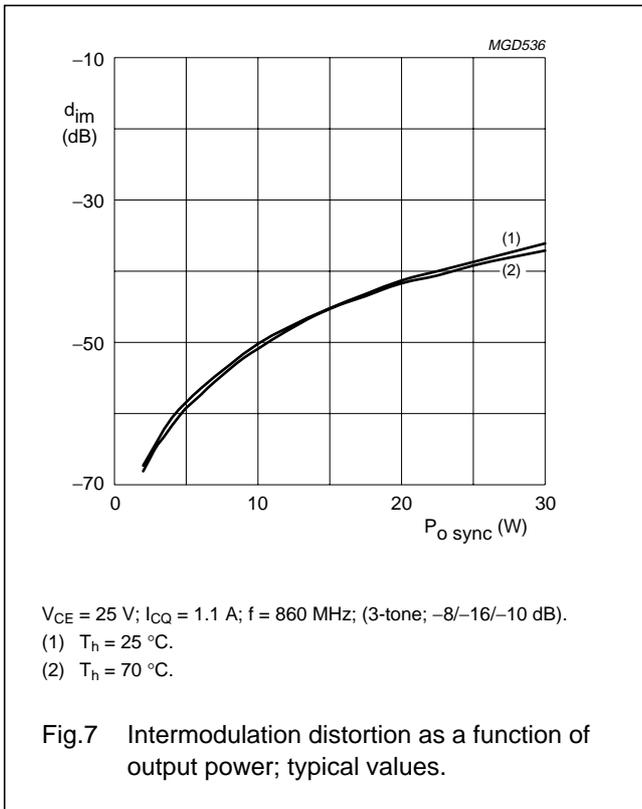
Ruggedness in class-A operation

The BLW898 is capable of withstanding a load mismatch corresponding to $VSWR = 50 : 1$ through all phases, under the conditions: $V_{CE} = 25\text{ V}$; $I_{CQ} = 1.1\text{ A}$; $T_h = 25\text{ }^\circ\text{C}$; $f = 860\text{ MHz}$; $P_{O\text{ sync}} = 3\text{ W}$.



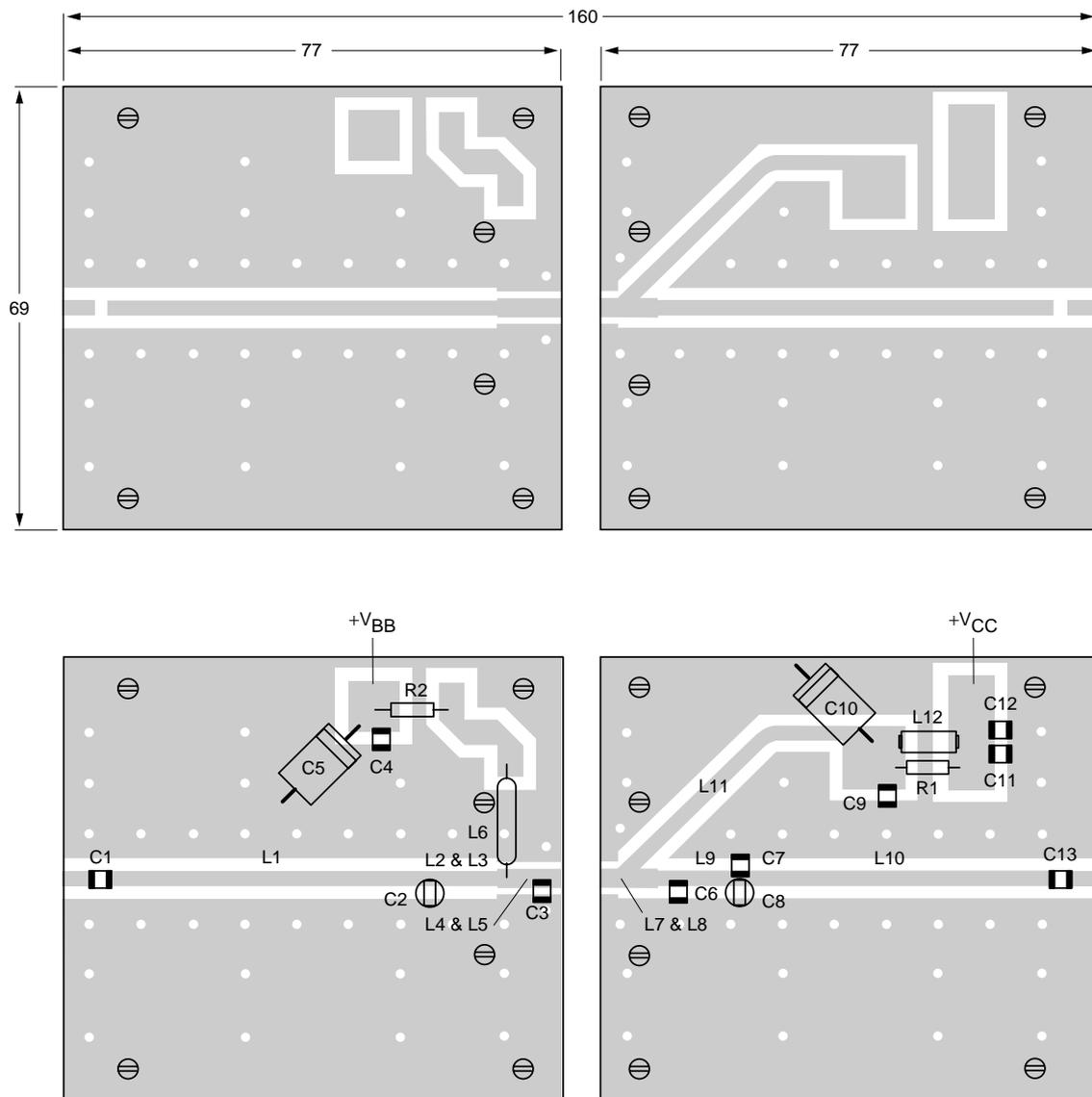
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MGD539

Dimensions in mm.

Fig.10 Printed-circuit board and component lay-out for 860 MHz class-A test circuit.

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List of components

| COMPONENT | DESCRIPTION | VALUE | DIMENSIONS | CATALOGUE No. |
|-----------|--|---------------------|-----------------------|----------------|
| C1 | multilayer ceramic chip capacitor; note 1 | 8.2 pF | | |
| C2, C8 | Tekelec Giga trim 37271 | 0.6 to 4.5 pF | | |
| C3 | multilayer ceramic chip capacitor; note 1 | 15 pF | | |
| C4, C12 | multilayer ceramic chip capacitor | 10 nF; 63 V | | 2222 592 16627 |
| C5 | solid aluminium capacitor | 10 μ F; 63 V | | 2222 030 38109 |
| C6 | multilayer ceramic chip capacitor; note 2 | 10 pF | | |
| C7 | multilayer ceramic chip capacitor; note 2 | 2.4 pF | | |
| C9 | multilayer ceramic chip capacitor; note 2 | 500 pF | | |
| C10 | solid aluminium capacitor | 47 μ F; 63 V | | 2222 031 38479 |
| C11 | multilayer ceramic chip capacitor; note 2 | 330 pF | | |
| C13 | multilayer ceramic chip capacitor; note 1 | 5.1 pF | | |
| L1 | stripline; note 3 | 50 Ω | 50 \times 2.3 mm | |
| L2 | stripline; note 3 | 50 Ω | 10 \times 2.3 mm | |
| L3 | stripline; note 3 | 40 Ω | 2 \times 3.25 mm | |
| L4, L5 | stripline; note 3 | 40 Ω | 4 \times 3.25 mm | |
| L6 | RF choke | 220 nH | | |
| L7 | stripline; note 3 | 40 Ω | 9 \times 3.25 mm | |
| L8 | stripline; note 3 | 40 Ω | 3.5 \times 3.25 mm | |
| L9 | stripline; note 3 | 50 Ω | 9 \times 2.3 mm | |
| L10 | stripline; note 3 | 50 Ω | 48.5 \times 2.3 mm | |
| L11 | stripline; note 3 | 40 Ω | 41.5 \times 3.25 mm | |
| L12 | grade 4S2 ferroxcube wideband RF choke | | | 4330 030 36301 |
| R1 | metal film resistor | 50 Ω ; 0.6 W | | 2322 156 14999 |
| R2 | metal film resistor | 10 Ω ; 0.6 W | | 2322 156 11009 |

Notes

1. American Technical Ceramics type 100A or capacitor of same quality.
2. American Technical Ceramics type 100B or capacitor of same quality.
3. The striplines are on a double copper-clad PCB with PTFE fibre-glass dielectric ($\epsilon_r = 2.2$); thickness 0.79 mm.

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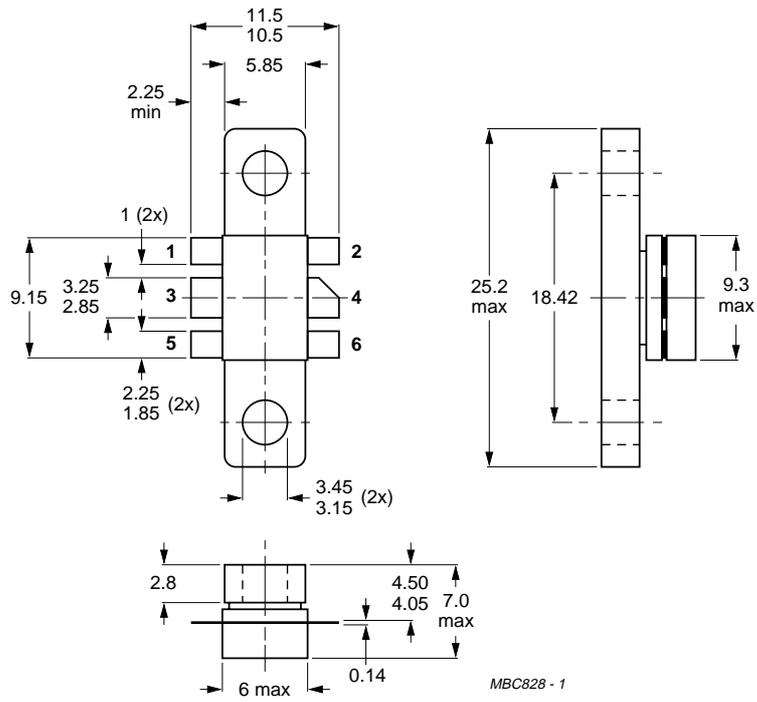
Table 1 Common emitter scattering parameter, $I_{CQ} = 1.1$ A; $V_{CE} = 25$ V.

| f (MHZ) | S ₁₁ | | S ₂₁ | | S ₁₂ | | S ₂₂ | | G _{UM} (dB) |
|------------|-----------------|---------------|-----------------|---------------|-----------------|---------------|-----------------|---------------|-------------------------|
| | MAG. (RAT) | ANG. (DEG) | MAG. (RAT) | ANG. (DEG) | MAG. (RAT) | ANG. (DEG) | MAG. (ANG) | ANG. (DEG) | |
| 470 | 0.962 | 176.1 | 1.002 | 68.3 | 0.017 | 32.6 | 0.802 | -178.2 | 15.7 |
| 495 | 0.961 | 175.9 | 0.961 | 66.9 | 0.017 | 32.8 | 0.803 | -178.2 | 15.2 |
| 520 | 0.959 | 175.7 | 0.923 | 65.7 | 0.017 | 33.6 | 0.804 | -178.2 | 14.7 |
| 545 | 0.958 | 175.5 | 0.891 | 64.4 | 0.018 | 34.9 | 0.803 | -178.3 | 14.3 |
| 570 | 0.957 | 175.3 | 0.861 | 63.2 | 0.018 | 35.8 | 0.804 | -178.2 | 14.0 |
| 595 | 0.955 | 175.0 | 0.835 | 62.0 | 0.018 | 36.1 | 0.805 | -178.2 | 13.5 |
| 620 | 0.953 | 174.8 | 0.815 | 61.0 | 0.019 | 36.8 | 0.804 | -178.2 | 13.0 |
| 645 | 0.951 | 174.5 | 0.795 | 59.7 | 0.019 | 37.3 | 0.805 | -178.1 | 12.7 |
| 670 | 0.950 | 174.2 | 0.775 | 58.6 | 0.019 | 37.4 | 0.807 | -178.0 | 12.5 |
| 695 | 0.947 | 173.9 | 0.757 | 57.7 | 0.020 | 37.8 | 0.806 | -178.0 | 12.0 |
| 720 | 0.943 | 173.7 | 0.744 | 56.6 | 0.021 | 38.5 | 0.805 | -178.1 | 11.5 |
| 745 | 0.942 | 173.4 | 0.732 | 55.4 | 0.021 | 38.6 | 0.807 | -177.9 | 11.3 |
| 770 | 0.941 | 173.1 | 0.724 | 54.4 | 0.021 | 39.8 | 0.808 | -177.8 | 11.1 |
| 795 | 0.938 | 172.8 | 0.716 | 53.3 | 0.021 | 40.1 | 0.807 | -177.8 | 10.8 |
| 820 | 0.935 | 172.5 | 0.707 | 51.8 | 0.022 | 39.1 | 0.808 | -177.8 | 10.6 |
| 845 | 0.933 | 172.1 | 0.701 | 50.9 | 0.021 | 39.3 | 0.810 | -177.6 | 10.4 |
| 860 | 0.932 | 171.9 | 0.700 | 50.2 | 0.022 | 39.4 | 0.809 | -177.5 | 10.3 |

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PACKAGE OUTLINE



MBC828 - 1

Dimensions in mm.

Fig.11 SOT171A.

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DEFINITIONS

| Data Sheet Status | |
|---|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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微波光电部专业代理经销高频、微波、光纤、光电元器件、组件、部件、模块、整机；电磁兼容元器件、材料、设备；微波 CAD、EDA 软件、开发测试仿真工具；微波、光纤仪器仪表。欢迎国外高科技微波、光纤厂商将优秀产品介绍到中国、共同开拓市场。长期大量现货专业批发高频、微波、卫星、光纤、电视、CATV 器件：晶振、VCO、连接器、PIN 开关、变容二极管、开关二极管、低噪晶体管、功率电阻及电容、放大器、功率管、MMIC、混频器、耦合器、功分器、振荡器、合成器、衰减器、滤波器、隔离器、环行器、移相器、调制解调器；光电子元件和组件：红外发射管、红外接收管、光电开关、光敏管、发光二极管和发光二极管组件、半导体激光二极管和激光器组件、光电探测器和光接收组件、光发射接收模块、光纤激光器和光放大器、光调制器、光开关、DWDM 用光发射和接收器件、用户接入系统光收发器件与模块、光纤连接器、光纤跳线/尾纤、光衰减器、光纤适配器、光隔离器、光耦合器、光环行器、光复用器/转换器；无线收发芯片和模组、蓝牙芯片和模组。

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